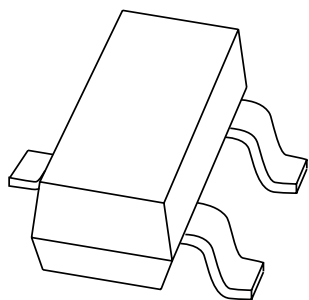


# DATA SHEET



## **BAS16** High-speed diode

Product specification  
Supersedes data of 1999 May 26

2001 Oct 10

# High-speed diode

## BAS16

### FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

### APPLICATIONS

- High-speed switching in hybrid thick and thin-film circuits.

### DESCRIPTION

The BAS16 is a high-speed switching diode fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BAS16	A6*

#### Note

- \* = p : Made in Hong Kong.  
\* = t : Made in Malaysia.  
\* = W : Made in China.

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

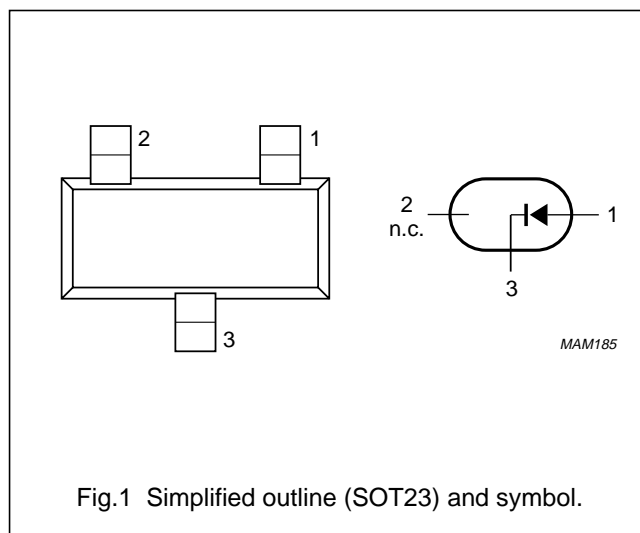
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	repetitive peak reverse voltage		–	85	V
$V_R$	continuous reverse voltage		–	75	V
$I_F$	continuous forward current	see Fig.2; note 1	–	215	mA
$I_{FRM}$	repetitive peak forward current		–	500	mA
$I_{FSM}$	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\text{ }\mu\text{s}$ $t = 1\text{ ms}$ $t = 1\text{ s}$	– – –	4 1 0.5	A A A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$ ; note 1	–	250	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C

#### Note

1. Device mounted on an FR4 printed-circuit board.

### PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode



## High-speed diode

## BAS16

**ELECTRICAL CHARACTERISTICS**

$T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$V_F$	forward voltage	see Fig.3 $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$ $I_F = 50\text{ mA}$ $I_F = 150\text{ mA}$	715 855 1 1.25	mV mV V V
$I_R$	reverse current	see Fig.5 $V_R = 25\text{ V}$ $V_R = 75\text{ V}$ $V_R = 25\text{ V}; T_j = 150\text{ °C}$ $V_R = 75\text{ V}; T_j = 150\text{ °C}$	30 1 30 50	nA $\mu\text{A}$ $\mu\text{A}$ $\mu\text{A}$
$C_d$	diode capacitance	$f = 1\text{ MHz}; V_R = 0$ ; see Fig.6	1.5	pF
$t_{rr}$	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$ ; $R_L = 100\text{ }\Omega$ ; measured at $I_R = 1\text{ mA}$ ; see Fig.7	4	ns
$V_{fr}$	forward recovery voltage	when switched from $I_F = 10\text{ mA}$ ; $t_r = 20\text{ ns}$ ; see Fig.8	1.75	V

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		330	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

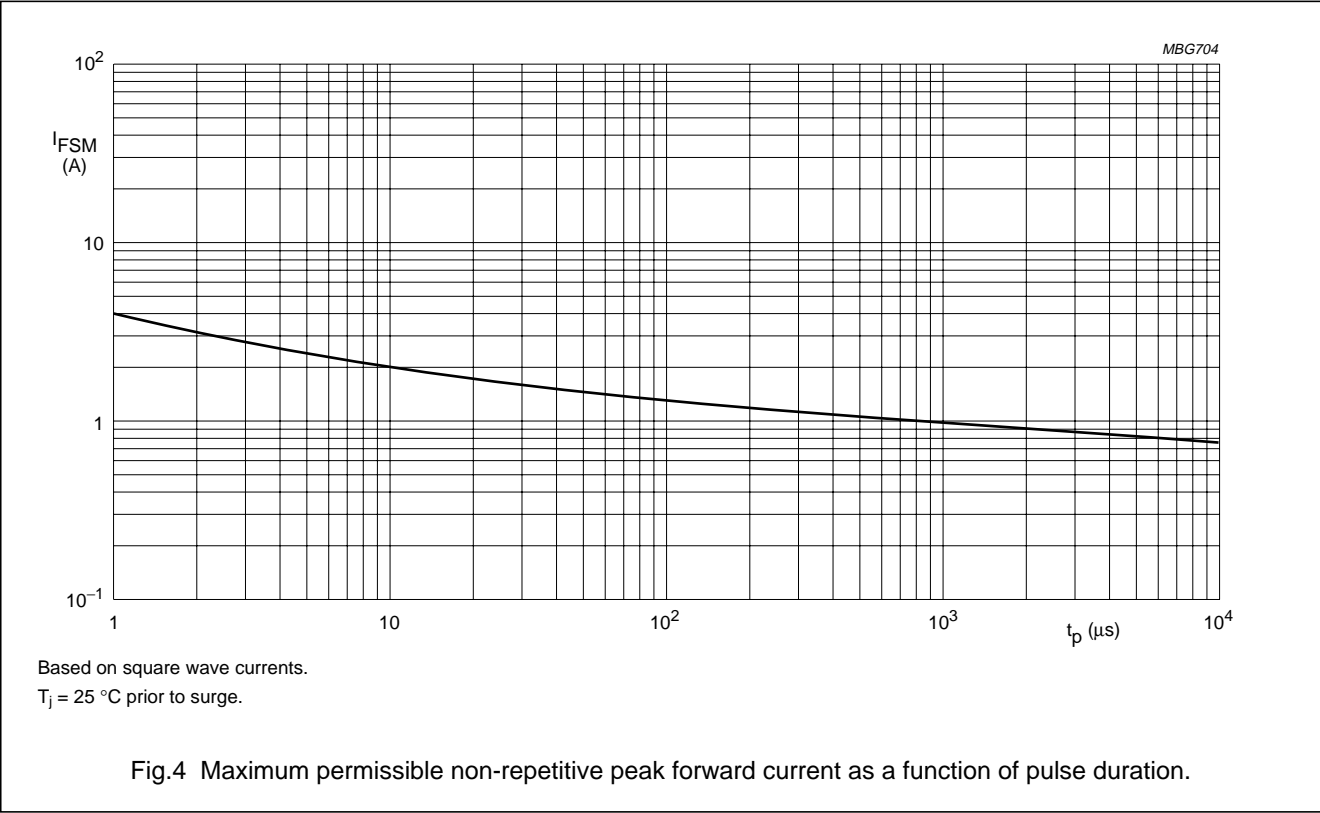
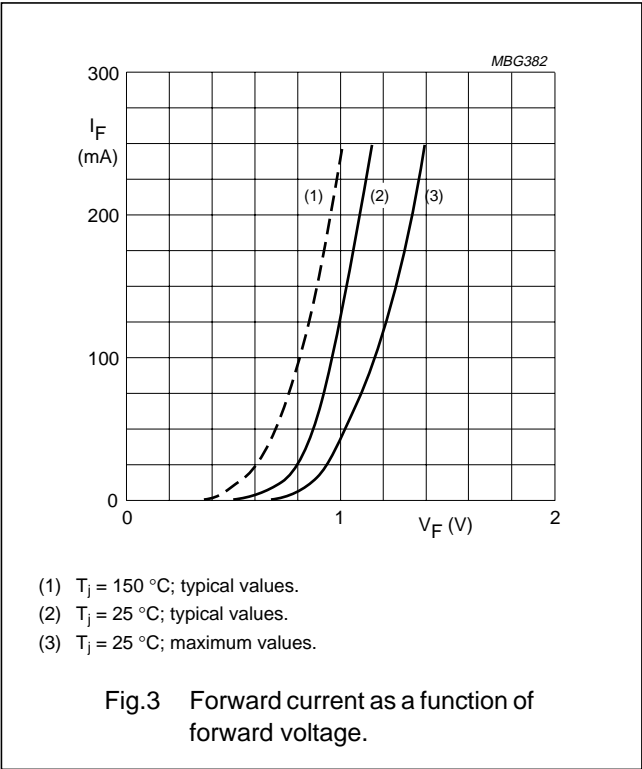
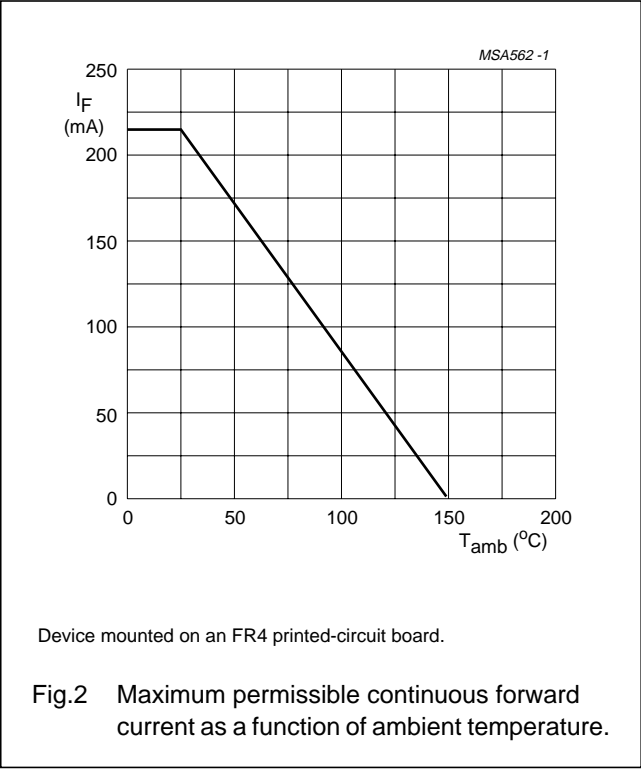
**Note**

1. Device mounted on an FR4 printed-circuit board.

High-speed diode

BAS16

GRAPHICAL DATA



High-speed diode

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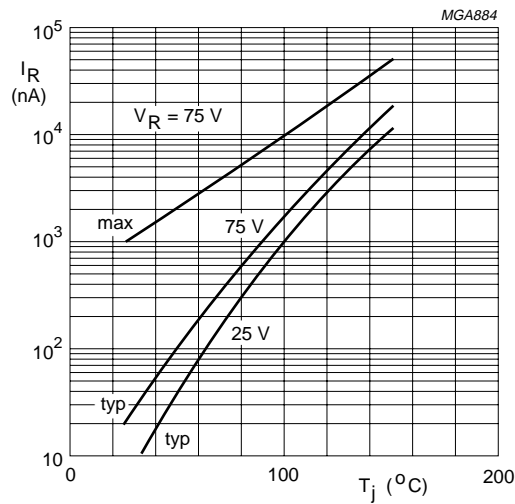
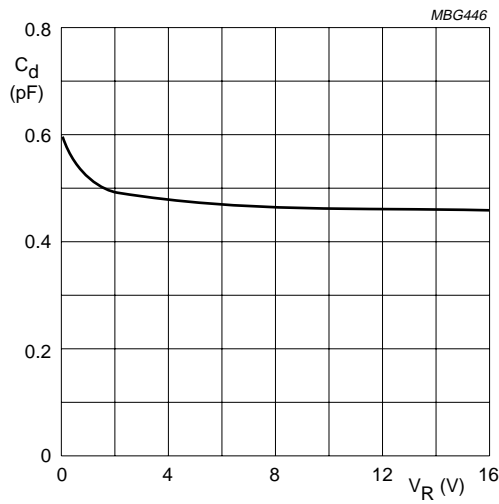


Fig.5 Reverse current as a function of junction temperature.

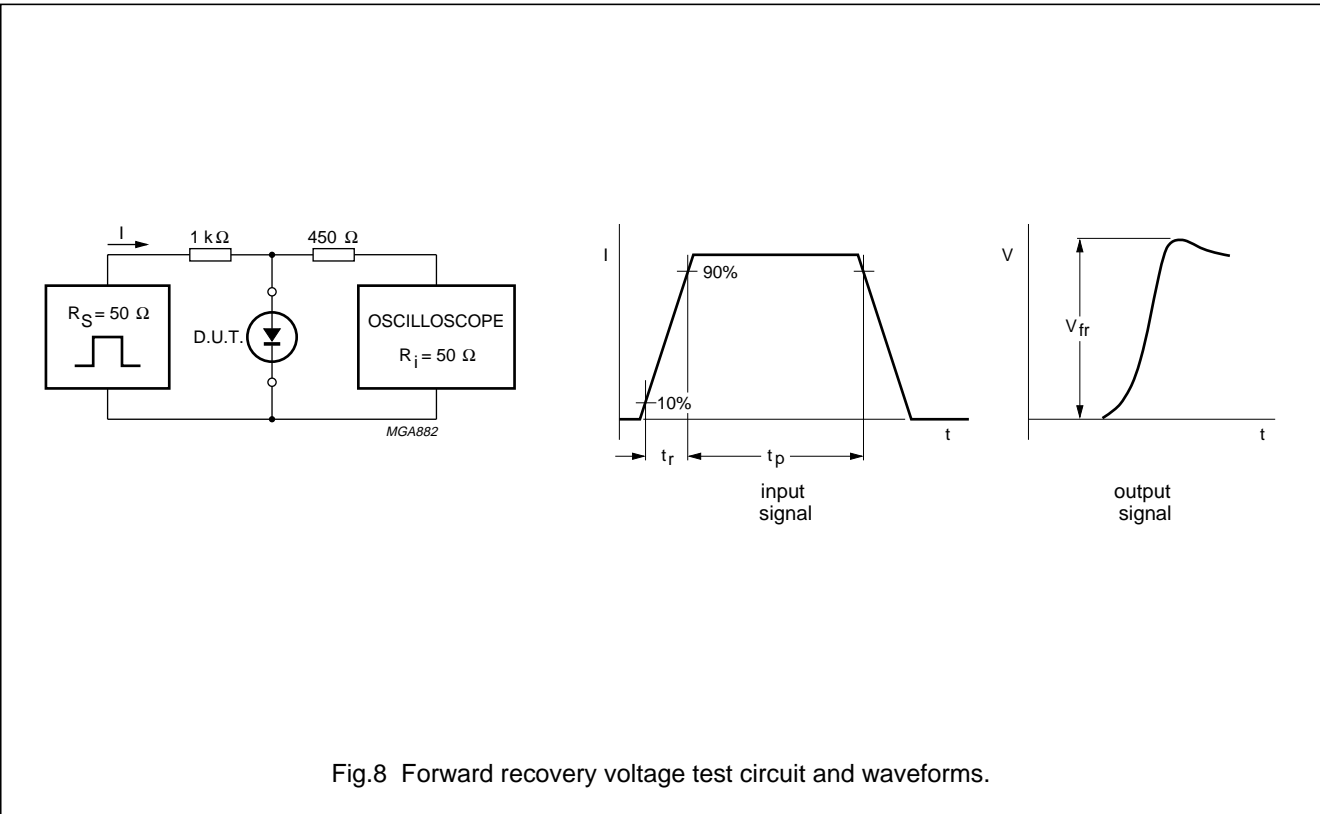
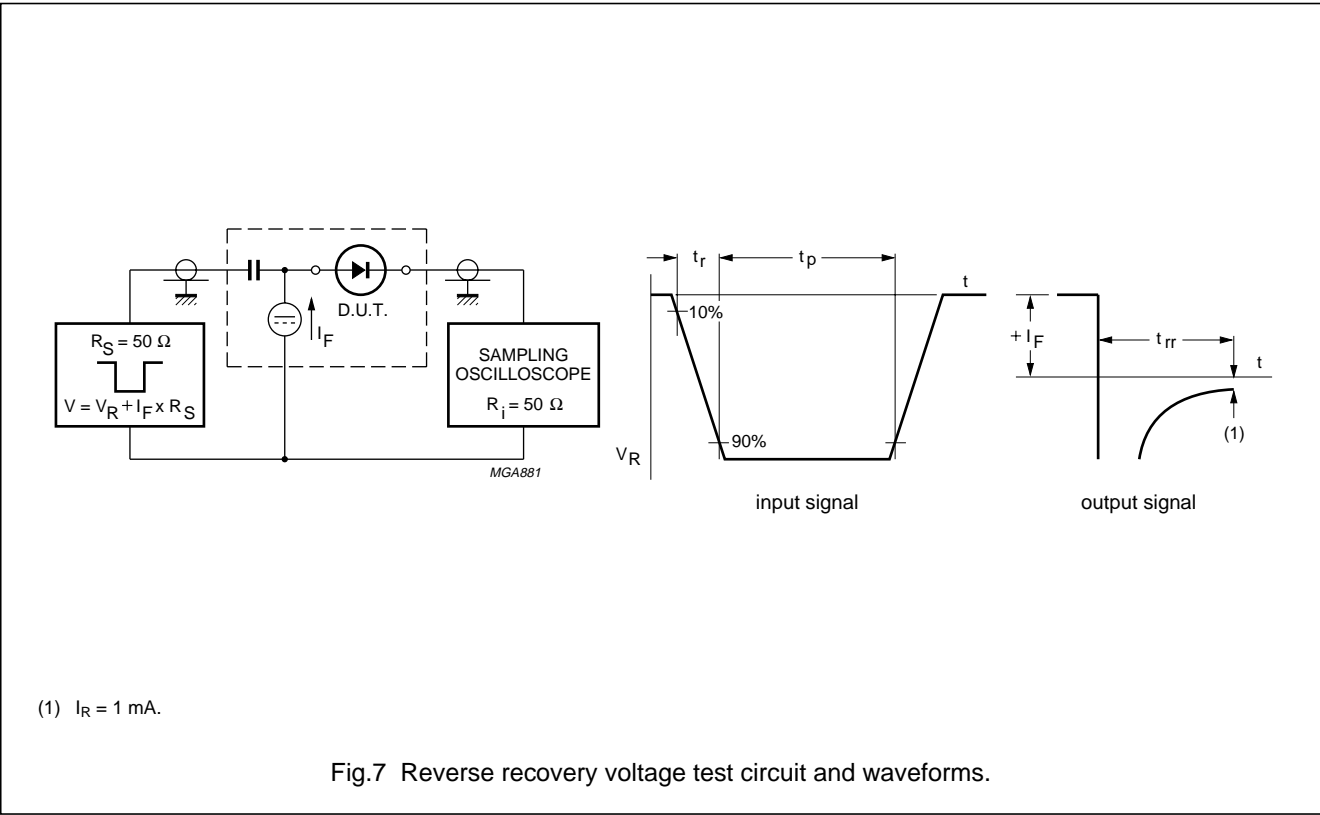


$f = 1\text{ MHz}$ ;  $T_j = 25\text{ °C}$ .

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

High-speed diode

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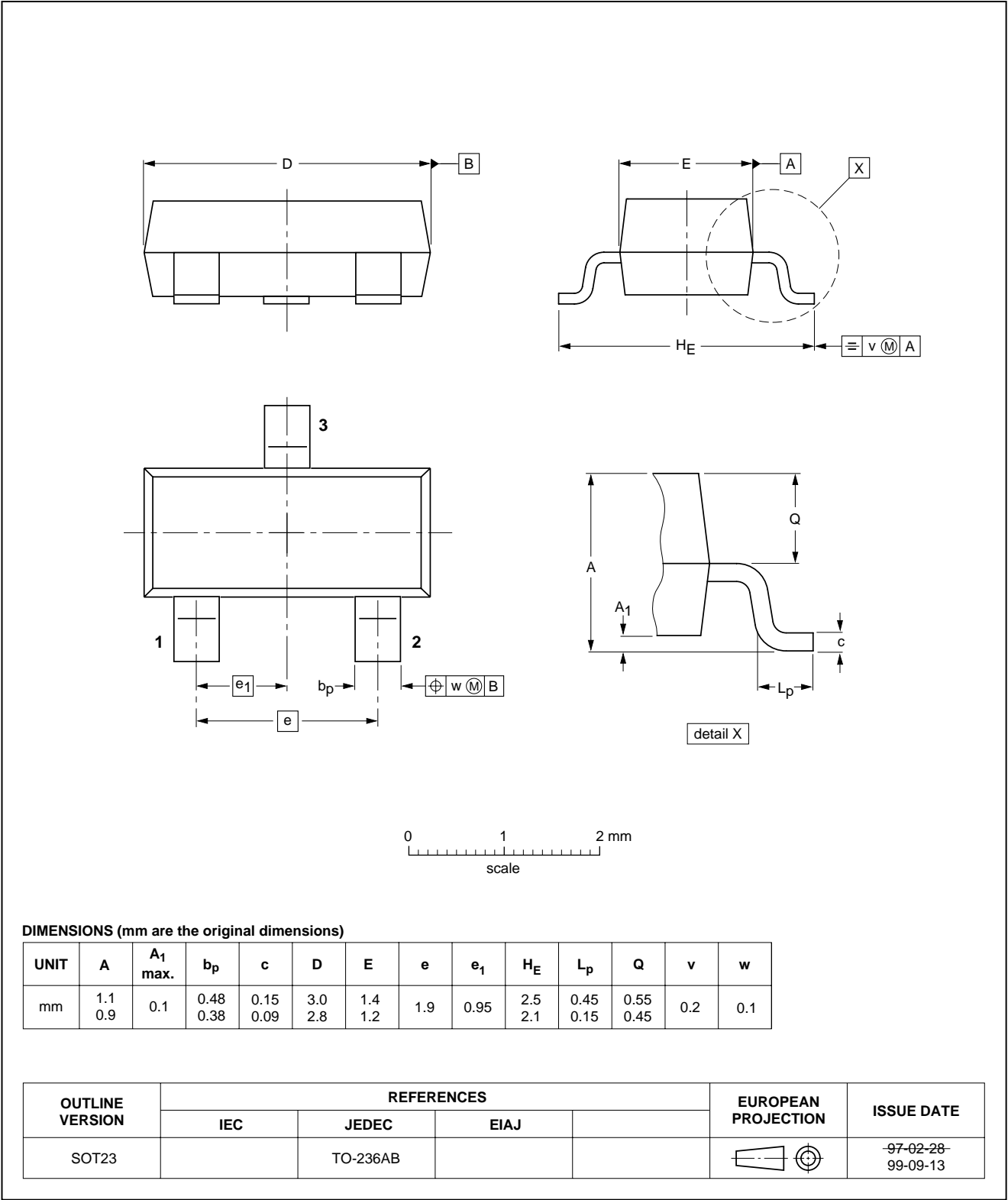
High-speed diode

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



## High-speed diode

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## DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

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High-speed diode

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**NOTES**

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**NOTES**

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